

Features

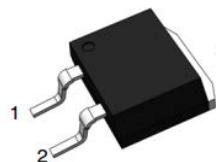
- Low reverse current
- Good surge current capability
- Low capacitive charge
- No reverse recovery current

V_{RRM}	=	1200 V
$I_F (T_c=153^\circ C)$	=	30 A
Q_C	=	150 nC

Benefits

- System efficiency improvement over Si diodes
- Higher switching frequency
- Increased power density
- Essentially no switching losses

Package



TO-263-2

Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- Motor drives
- UPS



Part Number	Package	Marking
ASZD030120G	TO-263-2	ASZD030120G

Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1200	V
V_{RSM}	Non-repetitive peak reverse voltage		1200	V
I_F	Continuous forward current	$T_c=25^\circ\text{C}$ $T_c=135^\circ\text{C}$ $T_c=153^\circ\text{C}$	79 42 30	A
I_{FRM}	Repetitive forward surge current	$T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse	86 58	A
I_{FSM}	Non-Repetitive forward surge current	$T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse	240 200	A
$\int i^2 dt$	$i^2 t$ value	$T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse	288 200	A^2s
P_{tot}	Power dissipation	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	300 130	W
T_j	Operating junction temperature		-55~175	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

Electrical Characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified)**Static Characteristics**

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{dc}	DC blocking voltage	$T_j=25^\circ\text{C}$	1200			V
V_F	Diode forward voltage	$I_F=30\text{A}$ $T_j=25^\circ\text{C}$ $I_F=30\text{A}$ $T_j=175^\circ\text{C}$		1.4 2.0	1.7	V
I_R	Reverse current	$V_R=1200\text{V}$ $T_j=25^\circ\text{C}$ $V_R=1200\text{V}$ $T_j=175^\circ\text{C}$			300 500	μA

AC Characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q_c	Total capacitive charge	$V_R=800\text{V}$ $T_j=25^\circ\text{C}$ $Q_c = \int_0^{V_R} C(V)dV$		150		nC
C	Total capacitance	$V_R=1\text{V}$ $f=1\text{MHz}$ $V_R=400\text{V}$ $f=1\text{MHz}$ $V_R=800\text{V}$ $f=1\text{MHz}$		2055 142 110		pF

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		0.50		$^\circ\text{C/W}$

Typical Performance

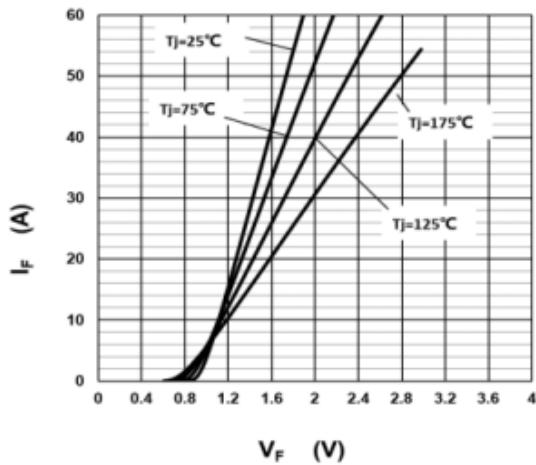


Figure 1. Typical forward characteristics

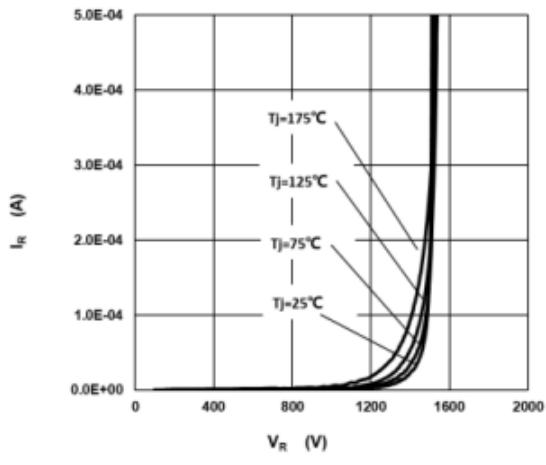


Figure 2. Typical reverse current as function of reverse voltage

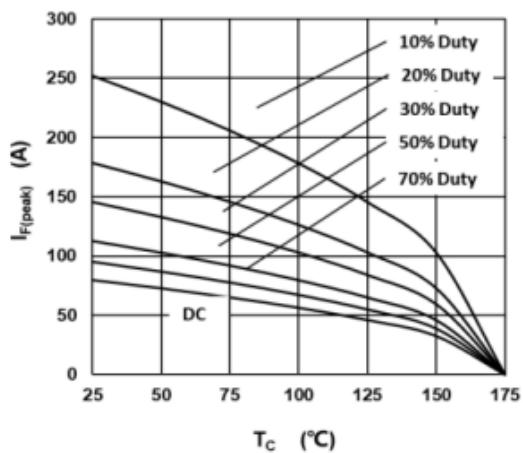


Figure 3. Diode forward current as function of temperature, D=duty cycle

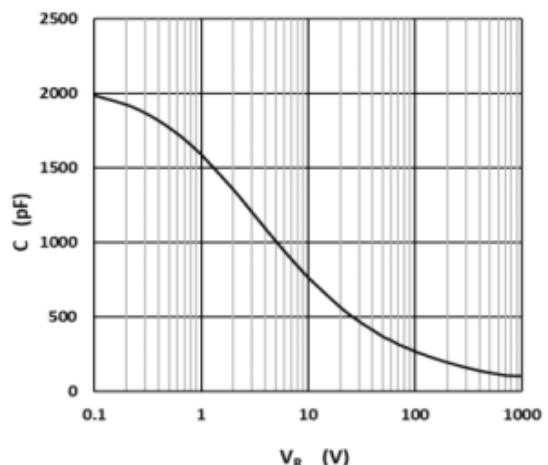


Figure 4. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_j=25^\circ\text{C}$

Typical Performance

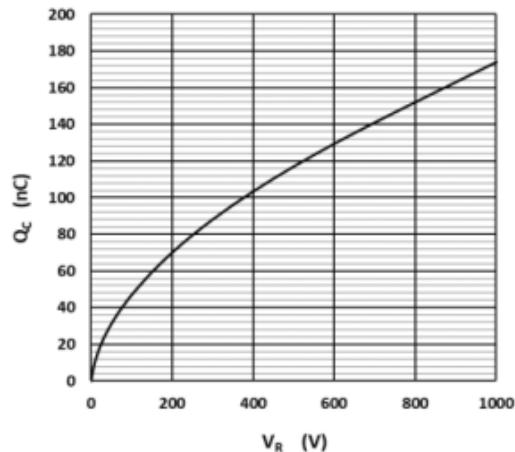


Figure 5. Typical reverse charge as function of reverse voltage

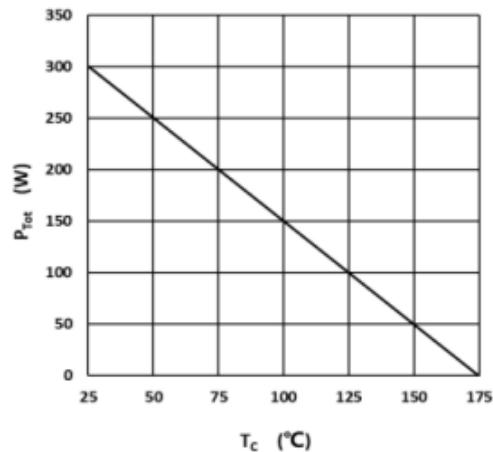


Figure 6. Power dissipation as function of case temperature

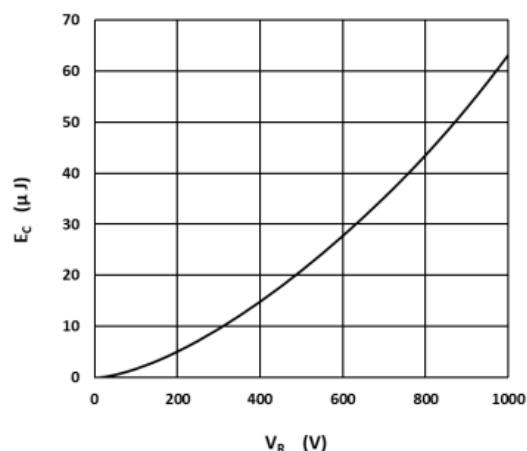


Figure 7. Capacitance stored energy

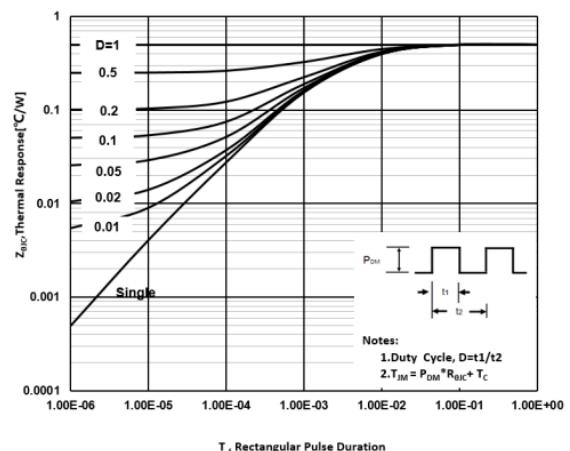
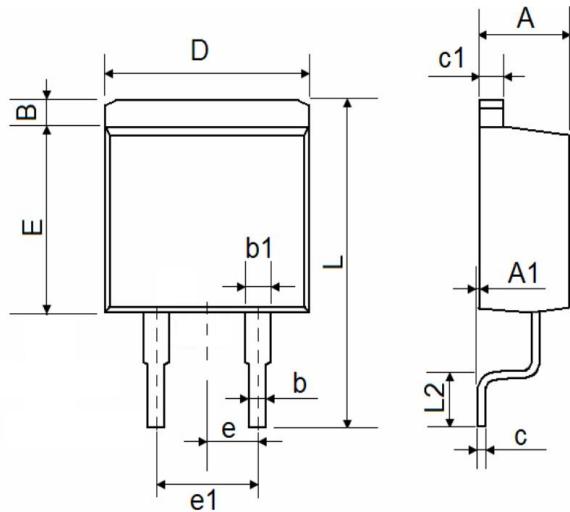


Figure 8. Max. transient thermal impedance

Package Dimensions

Package TO-263-2



Symbol	Min. (mm)	Typ. (mm)	Max. (mm)
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
c	0.40	0.50	0.60
c1	1.15	1.27	1.40
E	8.82	8.92	9.02
D	9.96	10.16	10.36
e	2.54 BSC		
e1	5.08 BSC		
L	14.61	15.00	15.88
L2	1.78	2.32	2.79
B	1.36 REF		